

BUK725R0-40C

N-channel TrenchMOS standard level FET

Rev. 01 — 23 March 2009

Product data sheet

1. Product profile

1.1 General description

Standard level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Avalanche robust
- Suitable for standard level gate drive
- Suitable for thermally demanding environment up to 175°C rating

1.3 Applications

- 12V Motor, lamp and solenoid loads
- High performance automotive power systems
- High performance Pulse Width Modulation (PWM) applications

1.4 Quick reference data

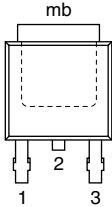
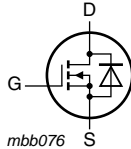
Table 1. Quick reference

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--|---|-----|-----|-----|------------|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$ | - | - | 40 | V |
| I_D | drain current | $V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ see Figure 1 ; see Figure 3 ; | [1] | - | 75 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C};$ see Figure 2 | - | - | 157 | W |
| Avalanche ruggedness | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 75\text{ A}; V_{sup} \leq 40\text{ V}; R_{GS} = 50\text{ }\Omega; V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C};$ unclamped | - | - | 240 | mJ |
| Dynamic characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; V_{DS} = 32\text{ V}; T_j = 25\text{ °C};$ see Figure 15 | - | 27 | - | nC |
| Static characteristics | | | | | | |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ see Figure 12 ; see Figure 13 | - | 4.1 | 5 | m Ω |

[1] Current is limited by package.

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|---|--|
| 1 | G | gate |  <p style="text-align: center;">SOT428 (SC-63; DPAK)</p> |  <p style="text-align: center;"><i>mbb076</i></p> |
| 2 | D | drain | | |
| 3 | S | source | | |
| mb | D | mounting base; connected to drain | | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | Version |
|--------------|----------------|---|---------|
| | Name | Description | |
| BUK725R0-40C | SC-63; DPAK | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit | |
|-----------------------------|--|---|---------------|-----|------|---|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$ | - | 40 | V | |
| V_{DGR} | drain-gate voltage | $R_{GS} = 20\text{ k}\Omega$ | - | 40 | V | |
| V_{GS} | gate-source voltage | | -20 | 20 | V | |
| I_D | drain current | $T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; see Figure 3 ; | [1] | - | 75 | A |
| | | $T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 | [1] | - | 75 | A |
| I_{DM} | peak drain current | $T_{mb} = 25\text{ °C}$; $t_p \leq 10\text{ }\mu\text{s}$; pulsed; see Figure 3 | - | 490 | A | |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C}$; see Figure 2 | - | 157 | W | |
| T_{stg} | storage temperature | | -55 | 175 | °C | |
| T_j | junction temperature | | -55 | 175 | °C | |
| Source-drain diode | | | | | | |
| I_S | source current | $T_{mb} = 25\text{ °C}$; | [2] | - | 75 | A |
| I_{SM} | peak source current | $t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$ | - | 490 | A | |
| Avalanche ruggedness | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 75\text{ A}$; $V_{sup} \leq 40\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped | - | 240 | mJ | |
| $E_{DS(AL)R}$ | repetitive drain-source avalanche energy | see Figure 4 | [3][4] [5] | - | J | |

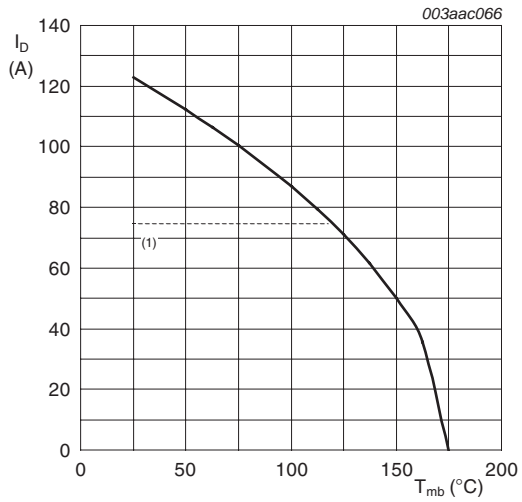
[1] Current is limited by package.

[2] Continuous current is limited by package.

[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

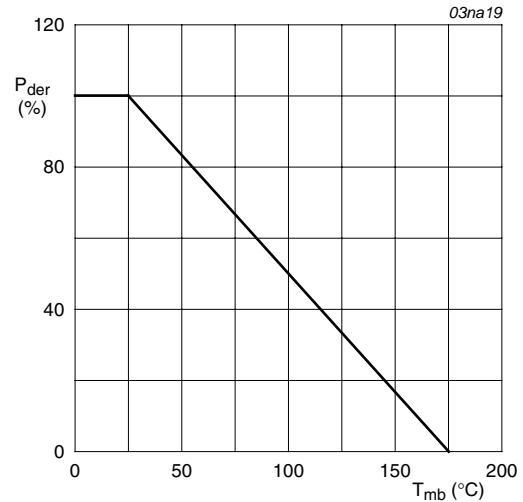
[4] Repetitive avalanche rating limited by average junction temperature of 170 °C.

[5] Refer to application note AN10273 for further information.



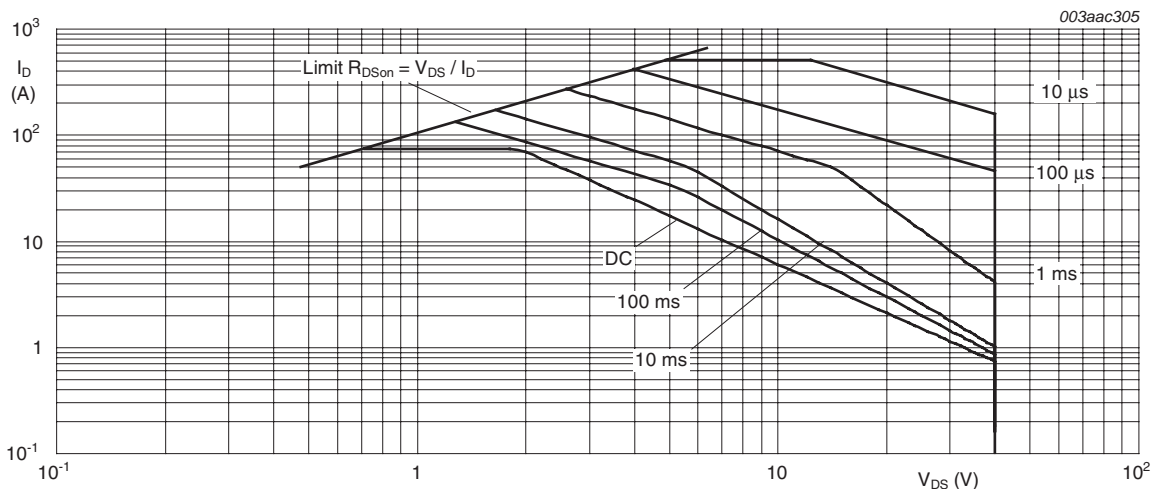
$V_{GS} \geq 10V$
 (1) Capped at 75 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature



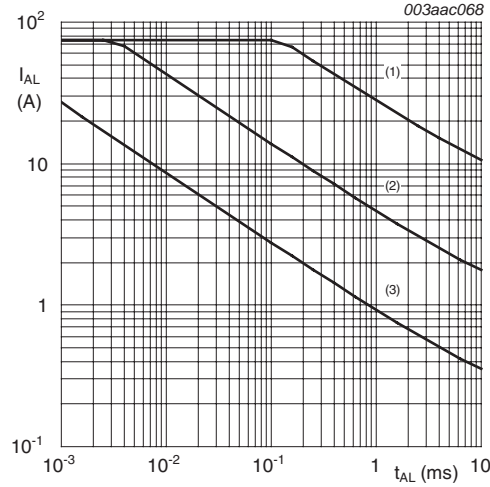
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^\circ C; I_{DM}$ is single pulse
 Capped at 75 A due to package.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



- (1) Single-pulse; $T_j = 25\text{ }^\circ\text{C}$.
- (2) Single-pulse; $T_j = 150\text{ }^\circ\text{C}$.
- (3) Repetitive.

Fig 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|---|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 5 | - | 0.65 | 0.95 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | vertical in still air; mounted on a printed circuit board; minimum foot-print | - | 70 | - | K/W |

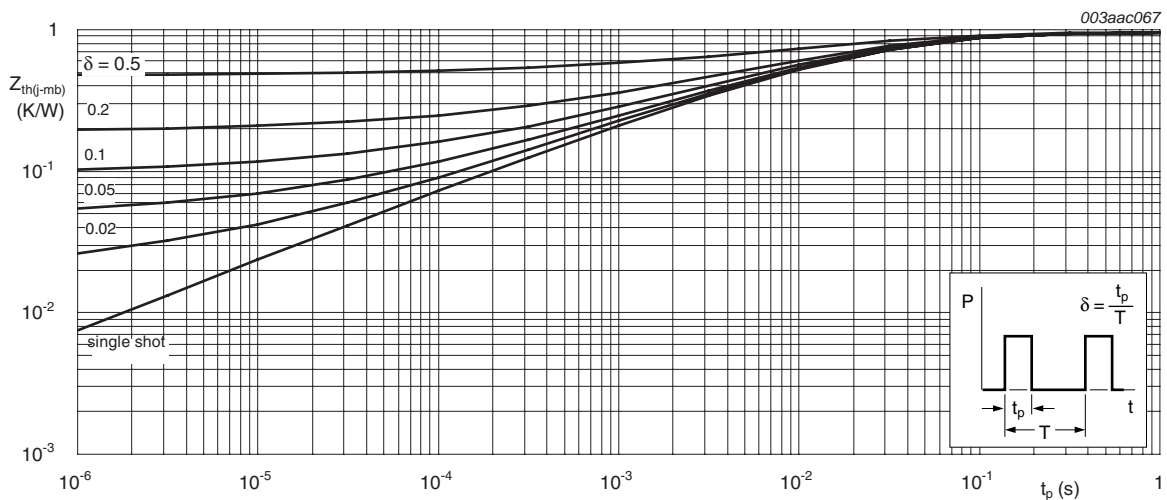
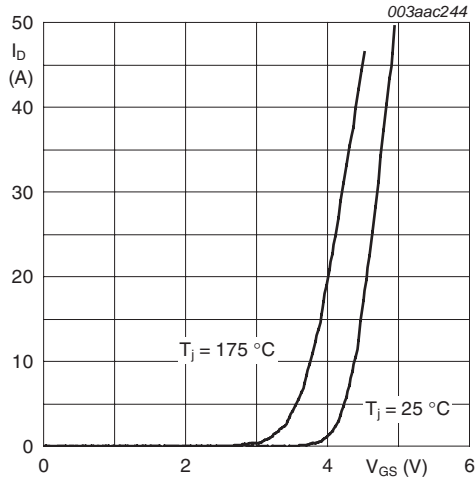


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

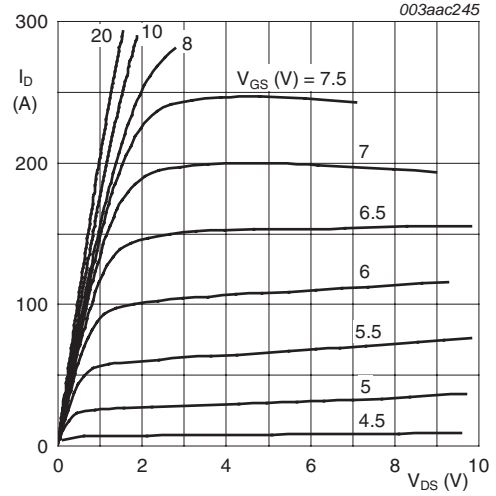
Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|--|-----|------|------|---------------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | 40 | - | - | V |
| | | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$ | 36 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 10 | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 10 | - | - | 4.4 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11 | 2 | 3 | 4 | V |
| I_{DSS} | drain leakage current | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$ | - | - | 500 | μA |
| | | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 0.05 | 1 | μA |
| I_{GSS} | gate leakage current | $V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 2 | 100 | nA |
| | | $V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 2 | 100 | nA |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 12 | - | - | 9.5 | m Ω |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 12 ; see Figure 13 | - | 4.1 | 5 | m Ω |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 15 | - | 60 | - | nC |
| Q_{GS} | gate-source charge | | - | 12 | - | nC |
| Q_{GD} | gate-drain charge | | - | 27 | - | nC |
| C_{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 16 | - | 2870 | 3820 | pF |
| C_{oss} | output capacitance | | - | 540 | 650 | pF |
| C_{rss} | reverse transfer capacitance | | - | 350 | 490 | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ }^\circ\Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 10 \text{ }^\circ\Omega; T_j = 25 \text{ }^\circ\text{C}$ | - | 27 | - | ns |
| t_r | rise time | | - | 73 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 82 | - | ns |
| t_f | fall time | | - | 63 | - | ns |
| L_D | internal drain inductance | measured from drain to centre of die; $T_j = 25 \text{ }^\circ\text{C}$ | - | 2.5 | - | nH |
| L_S | internal source inductance | measured from source lead to source bond pad; $T_j = 25 \text{ }^\circ\text{C}$ | - | 7.5 | - | nH |
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 14 | - | 0.85 | 1.2 | V |
| t_{rr} | reverse recovery time | $I_S = 20 \text{ A}; di_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = -10 \text{ V};$ $V_{DS} = 30 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 50 | - | ns |
| Q_r | recovered charge | | - | 25 | - | nC |



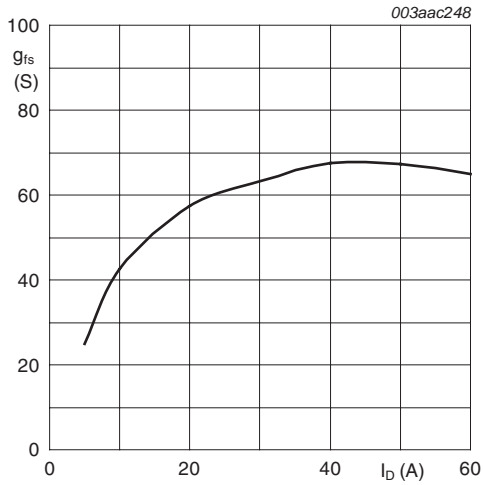
$V_{DS} = 25\text{ V}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



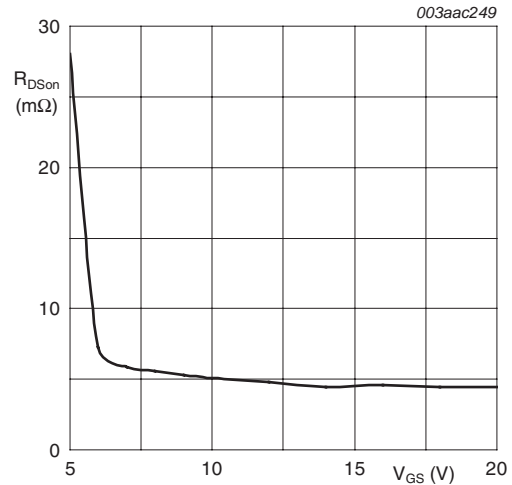
$T_j = 25^\circ\text{C}$

Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values



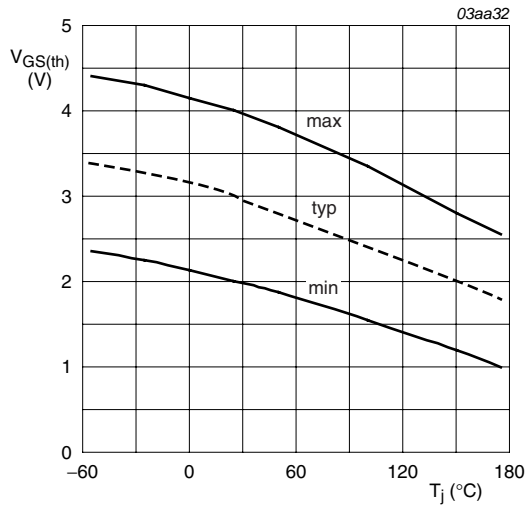
$T_j = 25^\circ\text{C}; V_{DS} = 25\text{ V}$

Fig 8. Forward transconductance as a function of drain current; typical values



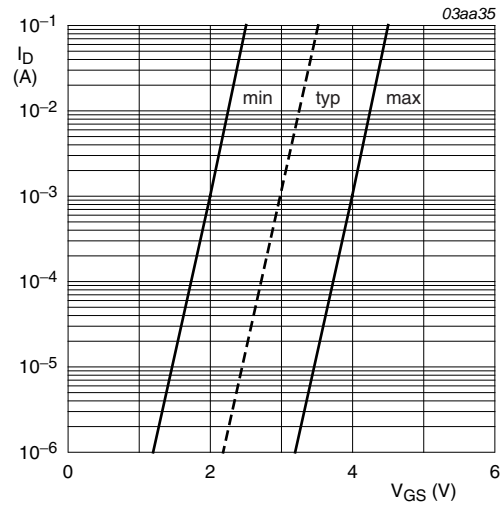
$T_j = 25^\circ\text{C}; I_D = 25\text{ A}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



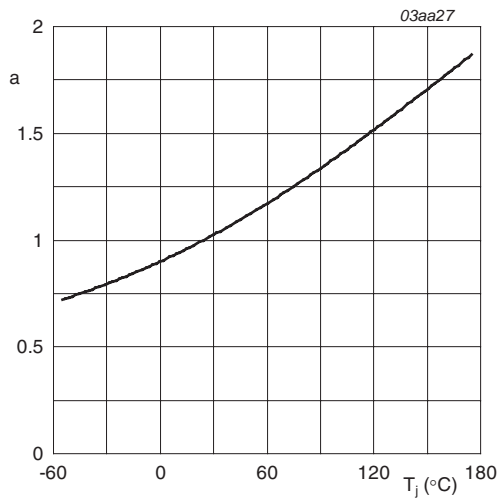
$$I_D = 1\text{ mA}; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature



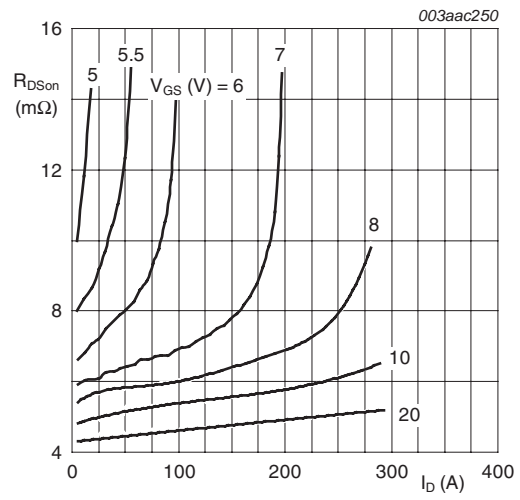
$$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



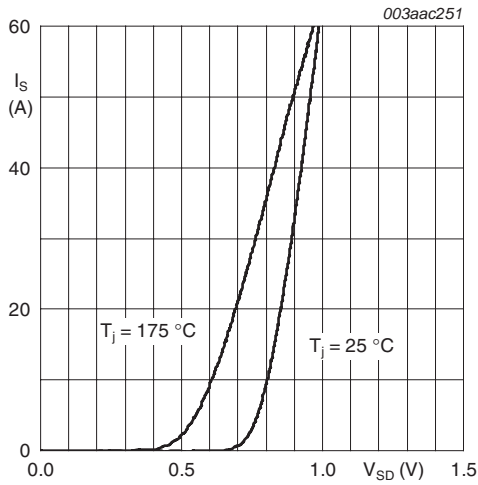
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



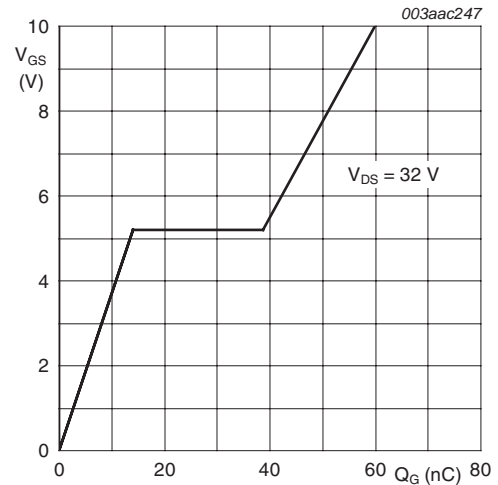
$$T_j = 25\text{ }^\circ\text{C}$$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values



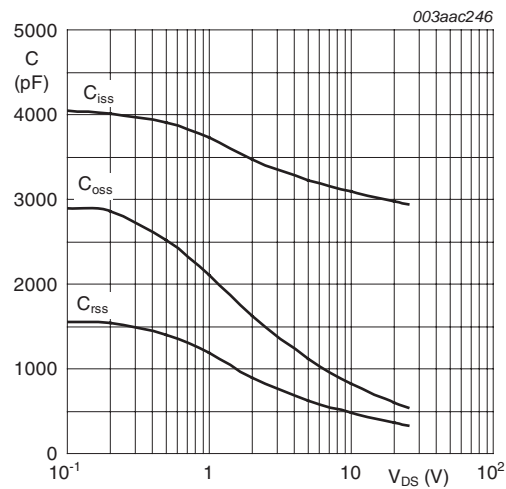
$V_{GS} = 0V$

Fig 14. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values



$T_j = 25\text{ }^\circ\text{C}; I_D = 25A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428

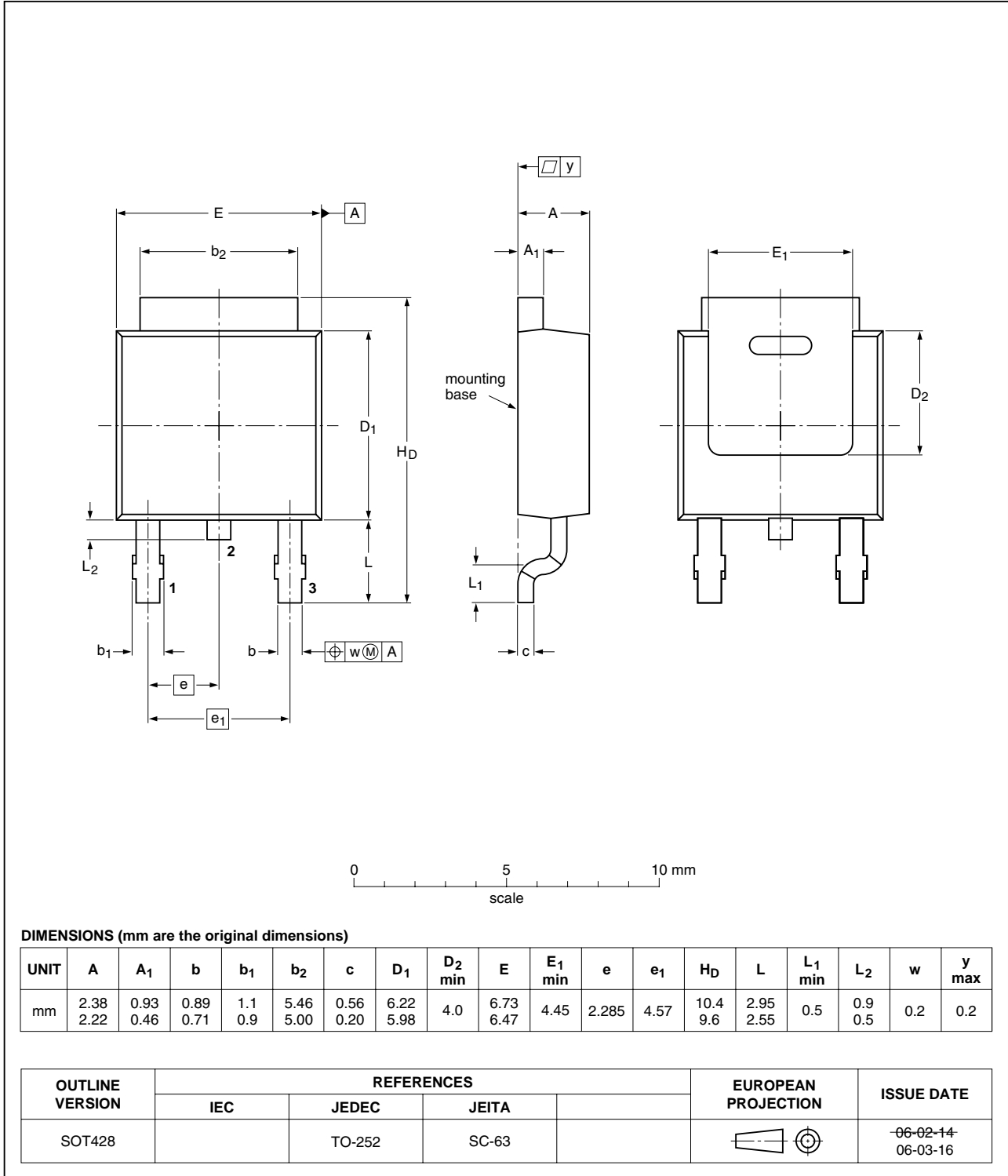


Fig 17. Package outline SOT428 (DPAK)

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| BUK725R0-40C_1 | 20090323 | Product data sheet | - | - |

9. Legal information

9.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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